

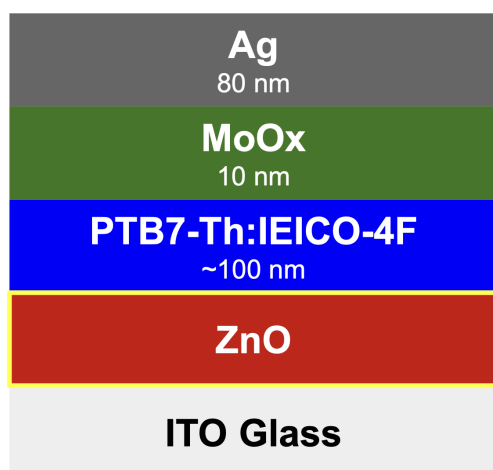


Figure 1: Device schematic. Four ZnO conditions were used: sol-gel annealed at 150°C for 30 min, 100°C ALD, 150°C ALD, and 180°C ALD.

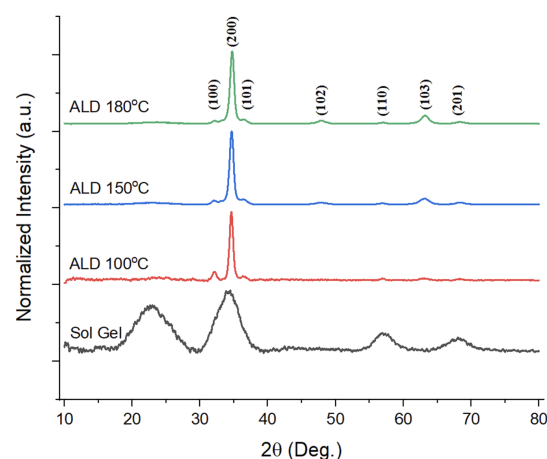


Figure 2: GIXRD for sol-gel and ALD-deposited ZnO. Improved crystallinity observed in ALD films, increasing with deposition temperature.

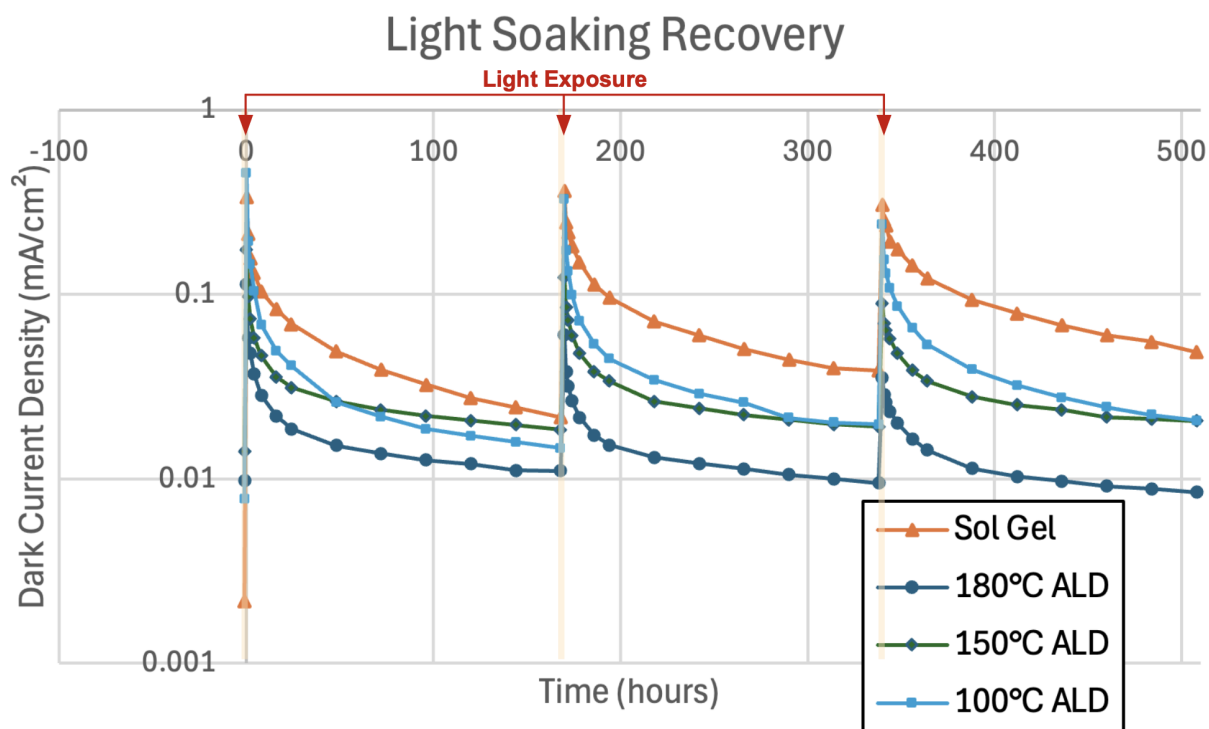


Figure 3: Dark current recovery after illumination for sol-gel and ALD ZnO OPDs. ALD devices show significantly faster recovery, indicating reduced persistent photoconductivity.